

HEF4020B-Q100

14-stage binary counter

Rev. 1 — 4 June 2014

Product data sheet

1. General description

The HEF4020B-Q100 is a 14-stage binary counter with a clock input (\overline{CP}), an overriding asynchronous master reset input (MR) and twelve fully buffered outputs (Q0, and Q3 to Q13). The counter advances on the HIGH to LOW transition of \overline{CP} . A HIGH on MR clears all counter stages and forces all outputs LOW, independent of the state of \overline{CP} . Each counter stage is a static toggle flip-flop. A feature of the device is its high speed (typ. 35 MHz at $V_{DD} = 15$ V).

It operates over a recommended V_{DD} power supply range of 3 V to 15 V referenced to V_{SS} (usually ground). Unused inputs must be connected to V_{DD} , V_{SS} , or another input.

This product has been qualified to the Automotive Electronics Council (AEC) standard Q100 (Grade 3) and is suitable for use in automotive applications.

2. Features and benefits

- Automotive product qualification in accordance with AEC-Q100 (Grade 3)
 - ◆ Specified from -40 °C to $+85$ °C
- High speed operation
- Fully static operation
- 5 V, 10 V, and 15 V parametric ratings
- Standardized symmetrical output characteristics
- ESD protection:
 - ◆ MIL-STD-883, method 3015 exceeds 2000 V
 - ◆ HBM JESD22-A114F exceeds 2000 V
 - ◆ MM JESD22-A115-A exceeds 200 V (C = 200 pF, R = 0 Ω)
- Complies with JEDEC standard JESD 13-B

3. Ordering information

Table 1. Ordering information

All types operate from -40 °C to $+85$ °C.

Type number	Package		Version
	Name	Description	
HEF4020BT-Q100	SO16	plastic small outline package; 16 leads; body width 3.9 mm	SOT109-1



4. Functional diagram

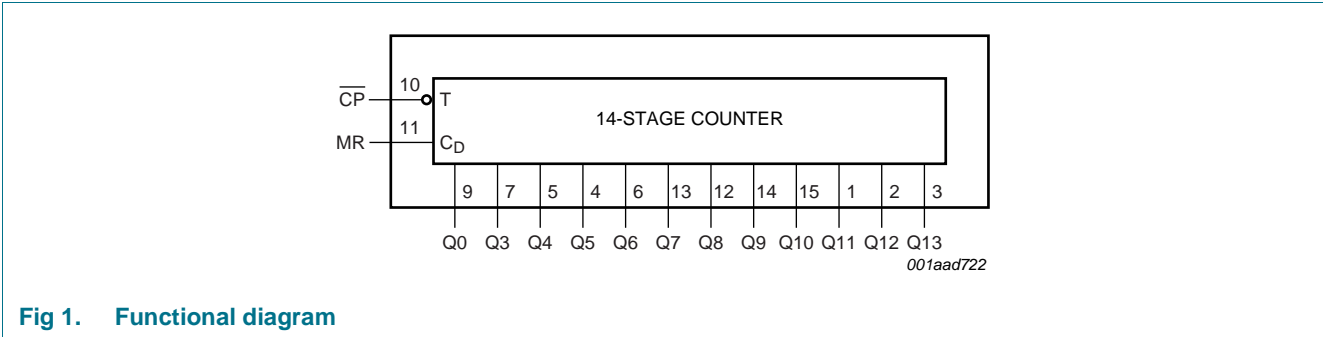


Fig 1. Functional diagram

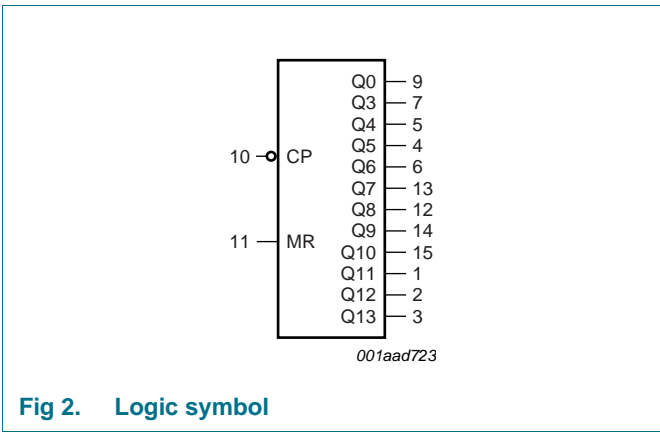


Fig 2. Logic symbol

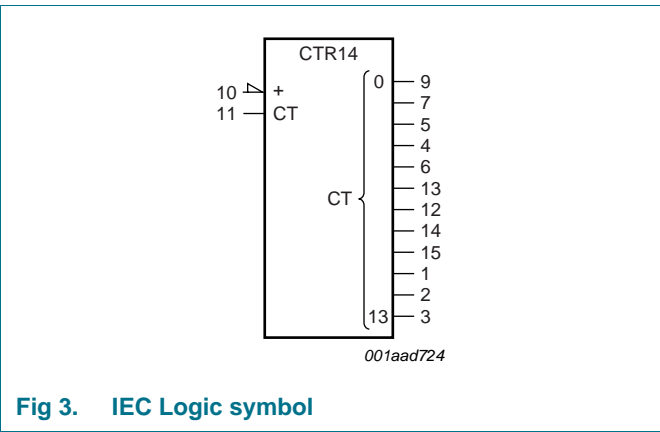


Fig 3. IEC Logic symbol

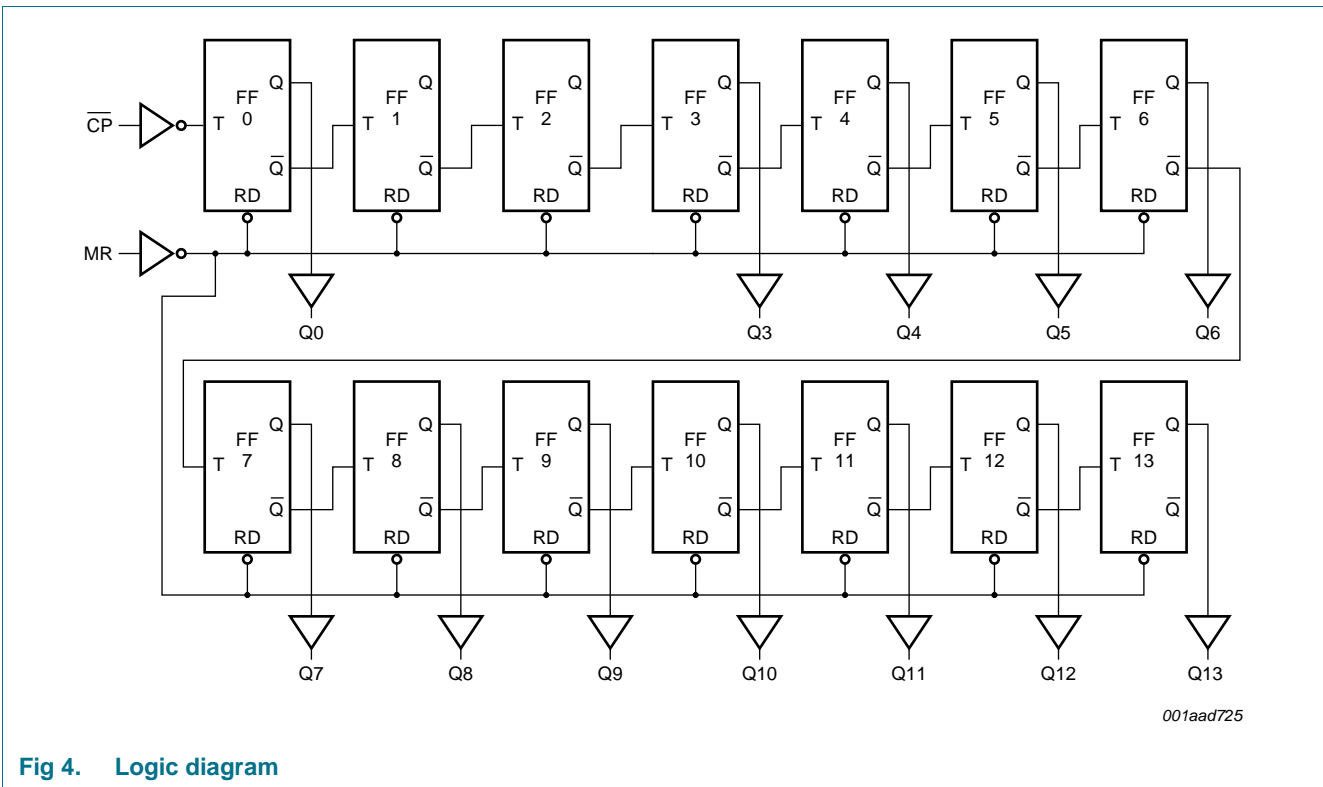
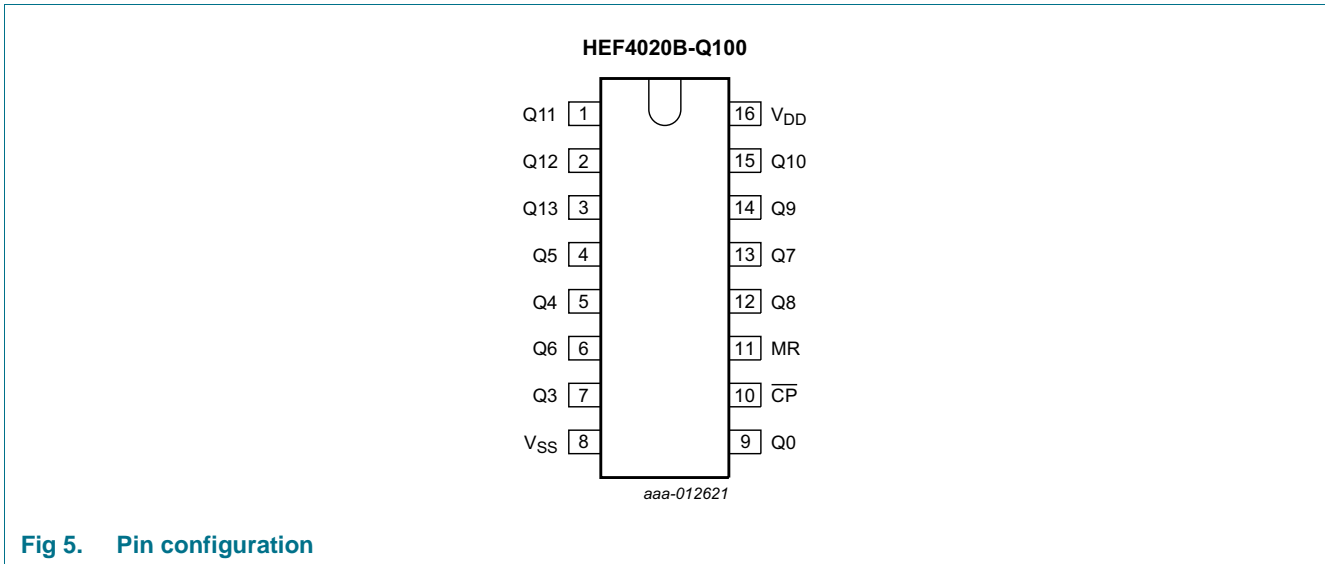


Fig 4. Logic diagram

5. Pinning information

5.1 Pinning



5.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
Q3 to Q13	7, 5, 4, 6, 13, 12, 14, 15, 1, 2, 3	parallel output (Q3 to Q13)
V _{SS}	8	ground supply voltage
Q0	9	parallel output
\overline{CP}	10	clock input (HIGH-to-LOW edge triggered)
MR	11	master reset input (active HIGH)
V _{DD}	16	supply voltage

6. Functional description

Table 3. Functional table^[1]

Input		Output
CP	MR	Q0, Q3 to Q13
↑	L	no change
↓	L	count
X	H	L

[1] H = HIGH voltage level; L = LOW voltage level; X = don't care; ↑ = positive-going transition; ↓ = negative-going transition.

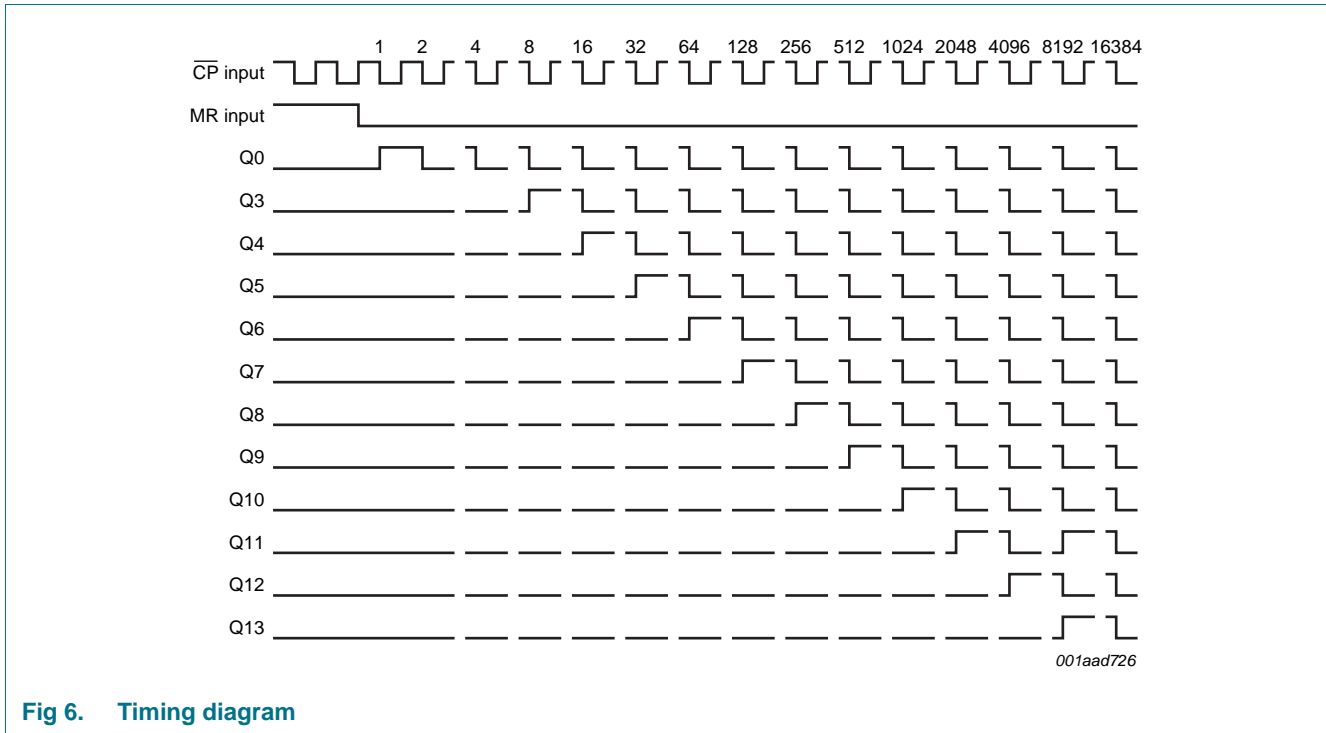


Fig 6. Timing diagram

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DD}	supply voltage		-0.5	+18	V
I_{IK}	input clamping current	$V_I < 0. -5 \text{ V}$ or $V_I > V_{DD} + 0.5 \text{ V}$	-	± 10	mA
V_I	input voltage		-0.5	$V_{DD} + 0.5$	V
I_{OK}	output clamping current	$V_O < -0.5 \text{ V}$ or $V_O > V_{DD} + 0.5 \text{ V}$	-	± 10	mA
$I_{I/O}$	input/output current		-	± 10	mA
I_{DD}	supply current		-	50	mA
T_{stg}	storage temperature		-65	+150	°C
T_{amb}	ambient temperature		-40	+85	°C
P_{tot}	total power dissipation	$T_{amb} -40 \text{ °C}$ to $+85 \text{ °C}$	[1]	500	mW
P	power dissipation	per output	-	100	mW

[1] For SO16 package: P_{tot} derates linearly with 8 mW/K above 70 °C.

8. Recommended operating conditions

Table 5. Recommended operating conditions

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DD}	supply voltage		3	-	15	V
V_I	input voltage		0	-	V_{DD}	V
T_{amb}	ambient temperature	in free air	-40	-	+85	°C
$\Delta t/\Delta V$	input transition rise and fall rate	$V_{DD} = 5\text{ V}$	-	-	3.75	$\mu\text{s/V}$
		$V_{DD} = 10\text{ V}$	-	-	0.5	$\mu\text{s/V}$
		$V_{DD} = 15\text{ V}$	-	-	0.08	$\mu\text{s/V}$

9. Static characteristics

Table 6. Static characteristics

$V_{SS} = 0\text{ V}$; $V_I = V_{SS}$ or V_{DD} ; unless otherwise specified.

Symbol	Parameter	Conditions	V_{DD}	$T_{amb} = -40\text{ °C}$		$T_{amb} = 25\text{ °C}$		$T_{amb} = 85\text{ °C}$		Unit
				Min	Max	Min	Max	Min	Max	
V_{IH}	HIGH-level input voltage	$ I_O < 1\ \mu\text{A}$	5 V	3.5	-	3.5	-	3.5	-	V
			10 V	7.0	-	7.0	-	7.0	-	V
			15 V	11.0	-	11.0	-	11.0	-	V
V_{IL}	LOW-level input voltage	$ I_O < 1\ \mu\text{A}$	5 V	-	1.5	-	1.5	-	1.5	V
			10 V	-	3.0	-	3.0	-	3.0	V
			15 V	-	4.0	-	4.0	-	4.0	V
V_{OH}	HIGH-level output voltage	$ I_O < 1\ \mu\text{A}$	5 V	4.95	-	4.95	-	4.95	-	V
			10 V	9.95	-	9.95	-	9.95	-	V
			15 V	14.95	-	14.95	-	14.95	-	V
V_{OL}	LOW-level output voltage	$ I_O < 1\ \mu\text{A}$	5 V	-	0.05	-	0.05	-	0.05	V
			10 V	-	0.05	-	0.05	-	0.05	V
			15 V	-	0.05	-	0.05	-	0.05	V
I_{OH}	HIGH-level output current	$V_O = 2.5\text{ V}$	5 V	-	-1.7	-	-1.4	-	-1.1	mA
		$V_O = 4.6\text{ V}$	5 V	-	-0.52	-	-0.44	-	-0.36	mA
		$V_O = 9.5\text{ V}$	10 V	-	-1.3	-	-1.1	-	-0.9	mA
		$V_O = 13.5\text{ V}$	15 V	-	-3.6	-	-3.0	-	-2.4	mA
I_{OL}	LOW-level output current	$V_O = 0.4\text{ V}$	5 V	0.52	-	0.44	-	0.36	-	mA
		$V_O = 0.5\text{ V}$	10 V	1.3	-	1.1	-	0.9	-	mA
		$V_O = 1.5\text{ V}$	15 V	3.6	-	3.0	-	2.4	-	mA
I_I	input leakage current		15 V	-	± 0.3	-	± 0.3	-	± 1.0	μA
I_{DD}	supply current	$I_O = 0\text{ A}$	5 V	-	20	-	20	-	150	μA
			10 V	-	40	-	40	-	300	μA
			15 V	-	80	-	80	-	600	μA
C_I	input capacitance		-	-	-	-	7.5	-	-	pF

10. Dynamic characteristics

Table 7. Dynamic characteristics

$V_{SS} = 0\text{ V}$; $T_{amb} = 25\text{ °C}$; for test circuit see [Figure 8](#).

Symbol	Parameter	Conditions	V_{DD}	Extrapolation formula ^[1]	Min	Typ	Max	Unit
t_{PHL}	HIGH to LOW propagation delay	CP to Q0; see Figure 7	5 V	$78\text{ ns} + (0.55\text{ ns/pF})C_L$	-	105	210	ns
			10 V	$34\text{ ns} + (0.23\text{ ns/pF})C_L$	-	45	90	ns
			15 V	$22\text{ ns} + (0.16\text{ ns/pF})C_L$	-	30	65	ns
		Qn to Qn + 1	5 V	$53\text{ ns} + (0.55\text{ ns/pF})C_L$	-	80	160	ns
			10 V	$19\text{ ns} + (0.23\text{ ns/pF})C_L$	-	30	60	ns
			15 V	$12\text{ ns} + (0.16\text{ ns/pF})C_L$	-	20	40	ns
		MR to Qn; see Figure 7	5 V	$153\text{ ns} + (0.55\text{ ns/pF})C_L$	-	180	360	ns
			10 V	$79\text{ ns} + (0.23\text{ ns/pF})C_L$	-	90	180	ns
			15 V	$62\text{ ns} + (0.16\text{ ns/pF})C_L$	-	70	140	ns
t_{PLH}	LOW to HIGH propagation delay	CP to Q0; see Figure 7	5 V	$78\text{ ns} + (0.55\text{ ns/pF})C_L$	-	105	210	ns
			10 V	$39\text{ ns} + (0.23\text{ ns/pF})C_L$	-	50	95	ns
			15 V	$27\text{ ns} + (0.16\text{ ns/pF})C_L$	-	35	70	ns
		Qn to Qn + 1	5 V	$43\text{ ns} + (0.55\text{ ns/pF})C_L$	-	70	140	ns
			10 V	$14\text{ ns} + (0.23\text{ ns/pF})C_L$	-	25	50	ns
			15 V	$12\text{ ns} + (0.16\text{ ns/pF})C_L$	-	20	40	ns
t_t	transition time	see Figure 7	5 V	$10\text{ ns} + (1.00\text{ ns/pF})C_L$	-	60	120	ns
			10 V	$9\text{ ns} + (0.42\text{ ns/pF})C_L$	-	30	60	ns
			15 V	$6\text{ ns} + (0.28\text{ ns/pF})C_L$	-	20	40	ns
t_w	pulse width	CP = HIGH; minimum width; see Figure 7	5 V		50	25	-	ns
			10 V		25	15	-	ns
			15 V		20	10	-	ns
		MR = HIGH; minimum width; see Figure 7	5 V		130	65	-	ns
			10 V		95	50	-	ns
			15 V		90	45	-	ns
t_{rec}	recovery time	MR input; see Figure 7	5 V		115	60	-	ns
			10 V		65	35	-	ns
			15 V		55	25	-	ns
f_{max}	maximum frequency	see Figure 7	5 V		5	10	-	MHz
			10 V		13	25	-	MHz
			15 V		18	35	-	MHz

[1] The typical values of the propagation delay and transition times are calculated from the extrapolation formulas shown (C_L in pF).

Table 8. Dynamic power dissipation P_D

P_D can be calculated from the formulas shown. $V_{SS} = 0\text{ V}$; $t_r = t_f \leq 20\text{ ns}$; $T_{amb} = 25\text{ }^\circ\text{C}$.

Symbol	Parameter	V_{DD}	Typical formula for P_D (μW)	where:
P_D	dynamic power dissipation	5 V	$P_D = 600 \times f_i + \Sigma(f_o \times C_L) \times V_{DD}^2$	f_i = input frequency in MHz, f_o = output frequency in MHz, C_L = output load capacitance in pF, V_{DD} = supply voltage in V, $\Sigma(f_o \times C_L)$ = sum of the outputs.
		10 V	$P_D = 2800 \times f_i + \Sigma(f_o \times C_L) \times V_{DD}^2$	
		15 V	$P_D = 8200 \times f_i + \Sigma(f_o \times C_L) \times V_{DD}^2$	

11. Waveforms

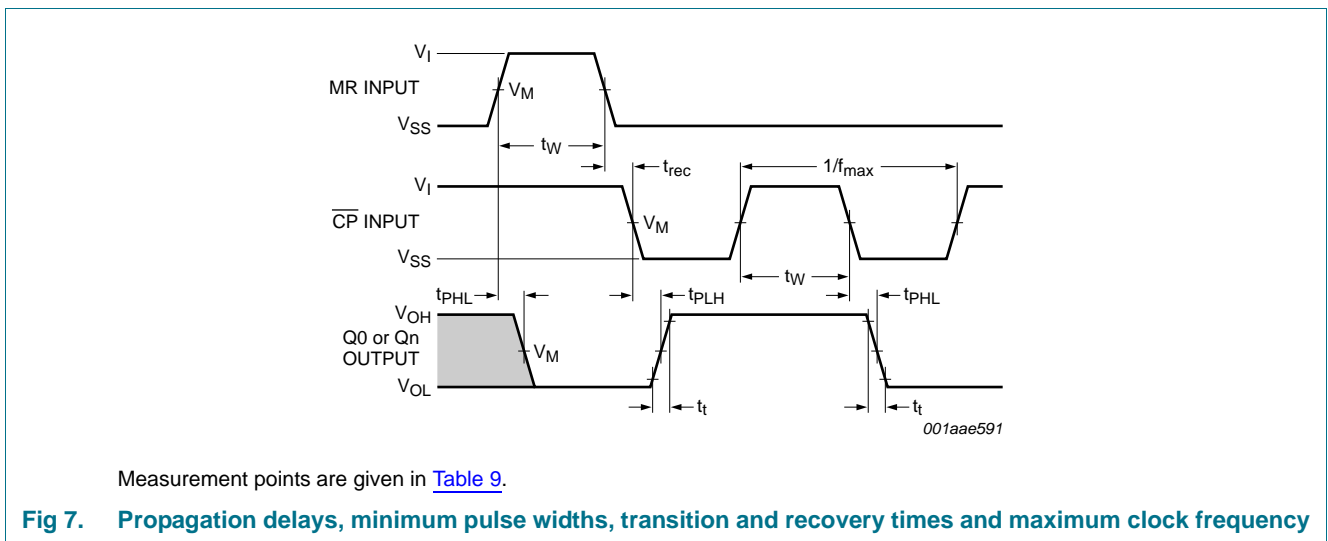
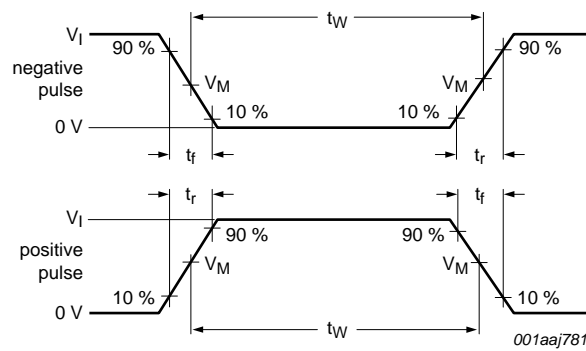
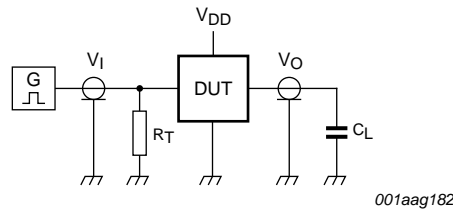


Table 9. Measurement points

Supply voltage	Input	Output
V_{DD}	V_M	V_M
5 V to 15 V	$0.5V_{DD}$	$0.5V_{DD}$



a. Input waveforms



b. Test circuit

Test data is given in [Table 10](#).

Definitions for test circuit:

DUT = Device Under Test.

C_L = load capacitance including jig and probe capacitance.

R_T = termination resistance should be equal to the output impedance Z_o of the pulse generator.

Fig 8. Test circuit for measuring switching times

Table 10. Test data

Supply voltage	Input		Load
V_{DD}	V_I	t_r, t_f	C_L
5 V to 15 V	V_{SS} or V_{DD}	≤ 20 ns	50 pF

12. Package outline

SO16: plastic small outline package; 16 leads; body width 3.9 mm

SOT109-1

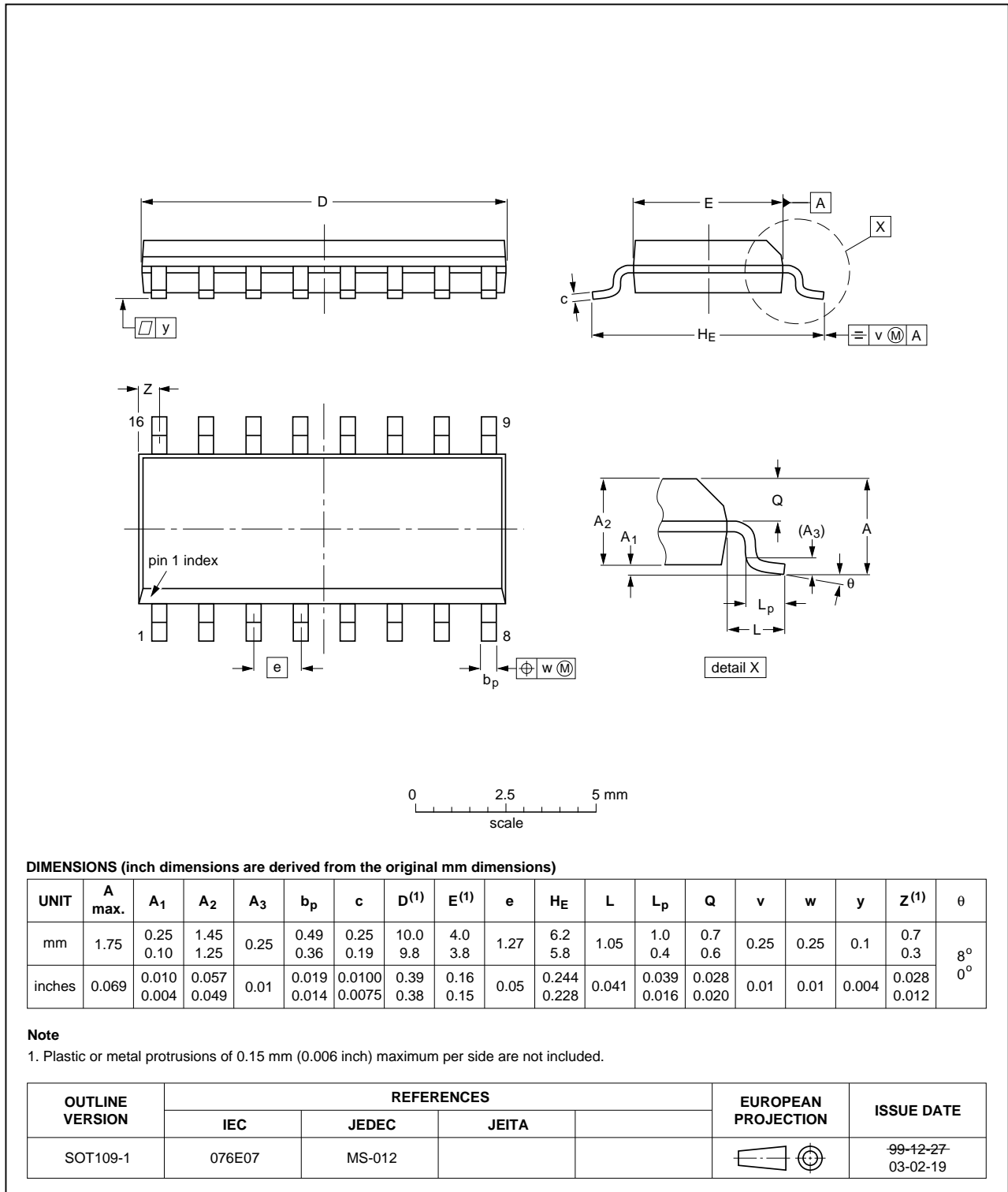


Fig 9. Package outline SOT109-1 (SO16)

13. Abbreviations

Table 11. Abbreviations

Acronym	Description
HBM	Human Body Model
ESD	ElectroStatic Discharge
MM	Machine Model
MIL	Military

14. Revision history

Table 12. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
HEF4020B_Q100 v.1	20140604	Product data sheet	-	-

15. Legal information

15.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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[2] The term 'short data sheet' is explained in section "Definitions".

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